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Tech ID: 22786

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ [Etching Technique for the Fabrication of Thin \(Al, In, Ga\)N Layers](#)
- ▶ [Lateral Growth Method for Defect Reduction of Semipolar Nitride Films](#)
- ▶ [Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation](#)
- ▶ [Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation](#)
- ▶ [III-Nitride-Based Vertical Cavity Surface Emitting Laser \(VCSEL\) with a Dielectric P-Side Lens](#)
- ▶ [Aluminum-cladding-free Nonpolar III-Nitride LEDs and LDs](#)
- ▶ [Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs \(UC Case 2010-183\)](#)
- ▶ [Implantable Light Irradiation Device For Photodynamic Therapy](#)
- ▶ [Low Temperature Deposition of Magnesium Doped Nitride Films](#)
- ▶ [Transparent Mirrorless \(TML\) LEDs](#)
- ▶ [Improved GaN Substrates Prepared with Ammonothermal Growth](#)
- ▶ [Optimization of Laser Bar Orientation for Nonpolar Laser Diodes](#)
- ▶ [Method for Enhancing Growth of Semipolar Nitride Devices](#)
- ▶ [Ultraviolet Laser Diode on Nano-Porous AlGaN template](#)
- ▶ [Growth of Polyhedron-Shaped Gallium Nitride Bulk Crystals](#)
- ▶ [Nonpolar III-Nitride LEDs With Long Wavelength Emission](#)
- ▶ [Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices](#)
- ▶ [Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films](#)
- ▶ [High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices](#)
- ▶ [Method for Growing High-Quality Group III-Nitride Crystals](#)
- ▶ [Controlled Photoelectrochemical \(PEC\) Etching by Modification of Local Electrochemical Potential of Semiconductor Structure](#)
- ▶ [Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices](#)
- ▶ [MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride](#)
- ▶ [Methods for Fabricating III-Nitride Tunnel Junction Devices](#)
- ▶ [Low-Droop LED Structure on GaN Semi-polar Substrates](#)
- ▶ [Contact Architectures for Tunnel Junction Devices](#)
- ▶ [Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface](#)
- ▶ [Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance](#)
- ▶ [III-Nitride-Based Devices Grown On Thin Template On Thermally Decomposed Material](#)
- ▶ [Growth of Semipolar III-V Nitride Films with Lower Defect Density](#)

- ▶ III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- ▶ Tunable White Light Based on Polarization-Sensitive LEDs
- ▶ Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
- ▶ Growth of High-Performance M-plane GaN Optical Devices
- ▶ Packaging Technique for the Fabrication of Polarized Light Emitting Diodes
- ▶ Improved Anisotropic Strain Control in Semipolar Nitride Devices
- ▶ Novel Multilayer Structure for High-Efficiency UV and Far-UV Light-Emitting Devices
- ▶ III-V Nitride Device Structures on Patterned Substrates
- ▶ Method for Increasing GaN Substrate Area in Nitride Devices
- ▶ High-Intensity Solid State White Laser Diode
- ▶ Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- ▶ GaN-Based Thermoelectric Device for Micro-Power Generation
- ▶ Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patterning
- ▶ LED Device Structures with Minimized Light Re-Absorption
- ▶ Growth of Planar Semi-Polar Gallium Nitride
- ▶ High-Efficiency and High-Power III-Nitride Devices Grown on or Above a Strain Relaxed Template
- ▶ UV Optoelectronic Devices Based on Nonpolar and Semi-polar AlInN and AlInGaN Alloys
- ▶ III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture
- ▶ Enhancing Growth of Semipolar (Al,In,Ga,B)N Films via MOCVD

